

This device is ready for take-off !



CONCLUSIONS

Fig. 5: D1, D2 and D3 SEE Cross-Section

Except for the embedded FROM, which is very radiation hard, all the other programmable architectures are sensitive to SEE SEU and SET hardening are achieved by the implementation of soft macros. There are no Single Event Functional Interrupts (SEFI) or Latch-ups (SEL) Gra complete SEE immunity at high frequencies (50 MHz and above), triplication of I/Os is mandatory in addition to their separation on 3 different IO banks. FPGA Core TID tolerance is hardened to 106krad(SiO₂) by a refresh scheme and the margining/programming circuit can withstand up to 40krad(SiO₂) As expected for a non-volatile FPGA, no observed error-event required a reconfiguration of the Flash-based FPGA nor were there any destructive SEE events

Fig. 15: FROM Block Diagram

REFERENCES

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Fig. 17: D1, D2 and D3 Electrical Parameters Degradation vs. TID of X-ray Irradiation for three A3P250-PQ208 DUTs

Fig. 16: FROM SEE Immunity

5. ProASIC®3L Low-Power Handbook: Available: http://www.actel.com/documents/PA3L_HB.pdf

Fig. 18: Refresh Effects on the A3P250 DUTs